## WHAT IS CLAIMED IS:

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- 1. A semiconductor device comprising:
- a lead electrode connecting to a lead wire;

a case electrode having a projecting wall portion around

a periphery thereof; and

a semiconductor chip disposed between said lead electrode and said case electrode with a bonding member interposed therebetween,

in opposing relation to said semiconductor chip and a second thickness region formed externally of said first region to be thinner than said first thickness region.

- 2. The semiconductor device according to claim 1, wherein said second thickness region has a thickness equal to or smaller than a thickness of said bonding member located between said lead electrode and said semiconductor chip.
- 3. The semiconductor device according to claim 1, wherein said first thickness region has a thickness equal to or smaller than three times a thickness of said bonding member located between said lead electrode and said semiconductor chip.
- 4. The semiconductor device according to claim 1, wherein said lead electrode further has a third thickness region thicker than said second thickness region and located externally of said second thickness region.
  - 5. A semiconductor device comprising:

- a lead electrode connecting to a lead wire;
- a case electrode having a wall portion on an outer peripheral portion thereof; and

a semiconductor chip disposed between said lead electrode and said case electrode with a bonding member interposed therebetween,

said lead electrode having a trenched portion formed in a surface of said lead electrode opposite to a surface thereof opposing said semiconductor chip and extending in a circumferential direction of said electrode.

6. A semiconductor device comprising:

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- a lead electrode connecting to a lead wire;
- a case electrode having a wall portion on an outer peripheral portion thereof; and

a semiconductor chip disposed between said lead electrode and said case electrode with a bonding member interposed therebetween,

said lead electrode having a first region located in a range to be bonded to said semiconductor chip with said bonding member interposed therebetween, a second region thinner than said first region and located at a larger distance from the lead wire than said first region, and a third region thicker than said second region and located at a larger distance from the lead wire than said second region.

7. The semiconductor device according to claim 6, wherein

said second region is formed such that a first distance in a direction connecting an edge of said second region closer to the lead wire and an outer circumferential edge of said second region is equal to or smaller than 0.5 times a distance between an edge of said third region closer to said lead wire and an outer circumferential edge of said third region.

- 8. The semiconductor device according to claim 6, wherein said second region is formed in a range corresponding to 0.5 times or less a distance between an edge of said third region closer to said lead wire and an outer circumferential edge of said third region.
- 9. The semiconductor device according to claim 6, wherein said first region is formed to have a thickness equal to or less than three times a thickness of said bonding member bonded to said lead electrode.
- 10. The semiconductor device according to claim 1, wherein a metal plate is disposed between said lead electrode and said semiconductor chip or between said semiconductor chip and said case electrode.

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